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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete if Known

Application Number	09/216,078
Filing Date	December 18, 1998
First Named Inventor	Ni, Cheng-Tsung, et. al.
Art Unit	2823
Examiner Name	J. Garcia
Attorney Docket Number	16517-003800

U.S. PATENT DOCUMENTS

Examiner	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code ² (if known)			
JAG	AA	US-4,144,100	03-13-1979	MacIver et al.	
JAG	AB	US-4,743,563	05-10-1988	Pfister et al.	
JAG	AC	US-4,748,131	05-31-1988	Zietlow, Thomas C.	
JAG	AD	US-4,748,134	05-31-1988	Holland et al.	
JAG	AE	US-4,948,742	08-14-1990	Nishimura et al.	
JAG	AF	US-5,330,920	07-19-1994	Soleimani et al.	
JAG	AG	US-5,385,630	01-31-1995	Philipossian et al.	
JAG	AH	US-5,460,693	10-24-1995	Moslehi, Medrad M.	
JAG	AI	US-5,480,828	01-02-1996	Hsu et al.	
JAG	AJ	US-5,614,421	03-25-1997	Yang, Sheng-Hsing	
	AK				
	AL	US-			
	AM	US-			
	AN	US-			
	AO	US-			
	AP	US-			
	AQ	US-			
	AR	US-			
	AS	US-			
	AT	US-			

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹		T ⁶
JAG	AU	Peter J. Wright et al., <i>The Effect of Fluorine in Silicon Dioxide Gate Dielectrics</i> , IEEE Transactions on Electron Devices, Vol. 36, No. 5, May, 1989, 10 pages.	<input type="checkbox"/>
JAG	AV	G. S. Verdi, C.M.S. Rauthan, B.C. Pathak and W.S. Khokle, "Properties of the Fluorine-Implanted Si-SiO ₂ (2) System," Solid-State Electronics vol. 34, No. 8, 1991, pp. 889-892.	<input type="checkbox"/>
JAG	AW	Xie-Wen Wang, Artur Balasinski and T. P. Ma, "Pre-Oxidation Fluorine Implantation into Si (Process-Related MOS Characteristics)", J. Electrochem Soc. Vol. 139, No. 1, Jan. 1992, pp. 238-241.	<input type="checkbox"/>
	AX		<input type="checkbox"/>
	AY		<input type="checkbox"/>
	AZ		<input type="checkbox"/>
	BA		<input type="checkbox"/>
	BB		<input type="checkbox"/>

Examiner
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J. Garcia

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December 10, 2003

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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